

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

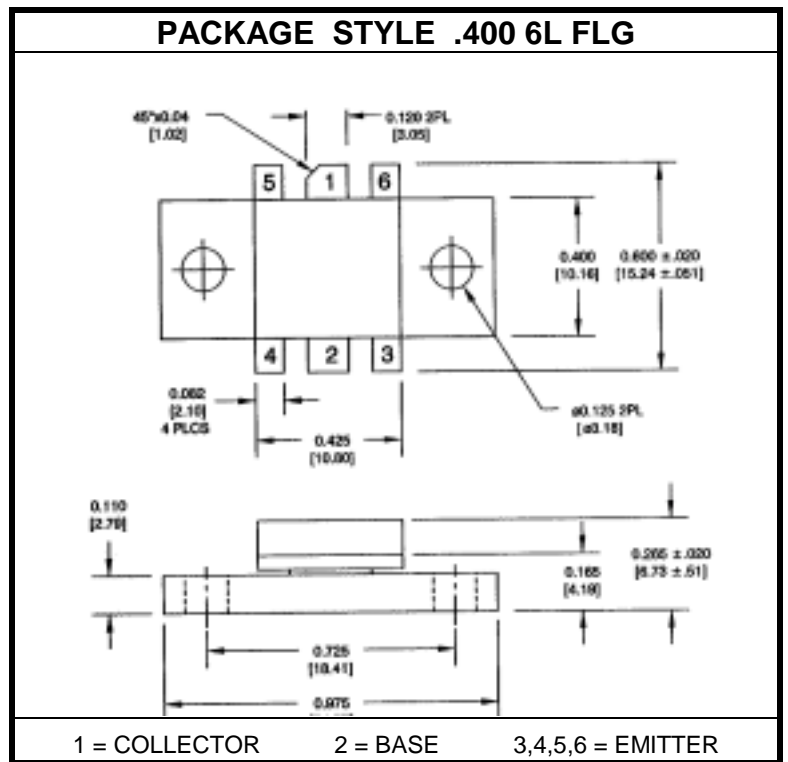
The **ASI PTB20038** is Designed for General Purpose Class AB Power Amplifier Applications up to 900 MHz.

FEATURES:

- 25 W, 860-900 MHz
- Silicon Nitride Passivated
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	6.7 A
V_{CB}	50 V
P_{DISS}	65 W @ $T_C = 25\text{ }^\circ\text{C}$
T_J	-40 $^\circ\text{C}$ to +150 $^\circ\text{C}$
T_{STG}	-40 $^\circ\text{C}$ to +150 $^\circ\text{C}$
θ_{JC}	2.7 $^\circ\text{C/W}$


CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100\text{ mA}$			25			V
BV_{CES}	$I_C = 100\text{ mA}$			55			V
BV_{EBO}	$I_E = 5.0\text{ mA}$			3.5			V
h_{FE}	$V_{CE} = 5.0\text{ V}$	$I_C = 1.0\text{ A}$		20		100	---
P_G	$V_{CC} = 25\text{ V}$	$P_{OUT} = 25\text{ W}$	$f = 900\text{ MHz}$	9.0			dB
η_c				50			%
P_G	$V_{CC} = 25\text{ V}$	$P_{OUT} = 10\text{ W}$	$f = 900\text{ MHz}$	10	11		dB
η_c	I_{CQ}			35			%
Ψ						30:1	---

